



FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE ATTY. DOCKET NO. EXPRESS MAIL NO. (REV.7-80) PATENT AND TRADEMARK OFFICE 850063.529 EL615231713US APPLICANTS INFORMATION DISCLOSURE STATEMENT Shin Hwa Li and Annie Tissier (Use several sheets if necessary) FILING DATE GROUP ART UNIT August 3, 2000 2823

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
1	AA	6,001,731	12/99	Su et al.	438	633	
16	AB	5,783,482	07/98	Lee et al.	438	624	
6	AC	5,437,763	08/95	Huang	216	18	
Lt.	AD	5,518,962	05/96	Murao	438	624	
16	ΑE	4,983,546	01/91	Hyun et al.	438	800	
Kt	AF	5,567,661	10/96	Nishio et al.	438	631	
4	AG**	5,169,491	12/92	Doan	156	636	
16	AH**	5,560,802	10/96	Chisholm	156	636.1	
K+	AI**	5,5661,084	08/97	Kuo et al.	438	624	

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	LATION
		NUMBER					YES	NO
11	AJ**	0599317A1	06/01/94	Europe	H01L	21/90		
V.F	AK**	09223740	08/26/97	Japan (Abstract Only)	H01L	21/768		
11/2	AL**	08255791 J	10/01/96	Japan (Abstract Only)	H01L	21/316		

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

VL	AM	Wolf, Stanley, PhD., Silicon Processing for the VLSI Era, Volume 2-Process Integration,
10	<u> </u>	Lattice Press, Sunset Beach, Volume 2: 334-337, 1990.
Kh	AN	Schaffer, W.J., et al., "BPSG Improves CPMP Performance for Deep Submicron Ics,"
Kr	}	Semiconductor International, 205-212, 1996.
VG	AO	Armstrong, W.E., et al., "A Scanning Electron Microscope Investigation of Glass Flow in
16	}	MOS Integrated Circuit Fabrication," Journal of the Electrochemical Society, Volume 121,
}	}	No. 2, 307-310, 1974.
14	AP	Kerr, D.R., et al., "Stabilization of SiO2 Passivation Layers with P2O5," IBM Journal of
16		Research and Development, Volume 8, No. 4, 376-384, 1964.

EXAMINER LITE EATON DATE CONSIDERED

* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).